IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

None of the claims have been cancelled or amended. The following is a list of all pending claims and their current status, for the convenience of the Examiner.

1. (PREVIOUSLY PRESENTED) A display device with a polysilicon substrate, comprising:

a display region;

a driving region;

a first plurality of thin film transistors in the display region;

a second plurality of thin film transistors in the driving region;

primary crystal grain boundaries in the polysilicon substrate in the display region and in the driving region;

secondary crystal grain boundaries in the polysilicon substrate in the display region and in the driving region;

wherein the primary crystal grain boundaries are inclined to a first direction of current flowing from source to drain of each of the first plurality of thin film transistors at an angle of -30° to 30° and the secondary crystal grain boundaries are inclined to a second direction of current flowing from source to drain of each of the first plurality of thin film transistors, and

wherein the primary crystal grain boundaries are inclined to the second direction of current flowing from source to drain of each of the second plurality of thin film transistors at an angle of 30° to 150° and the secondary crystal grain boundaries are inclined to the first direction of the current flowing from source to drain of each of the second plurality of thin film transistors.

2. (ORIGINAL) The display device according to claim 1, wherein the primary crystal grain boundaries are parallel to the first direction of current.

3. (ORIGINAL) The display device according to claim 2, wherein a first number of the primary crystal grain boundaries exist in active channel regions of each of the first plurality of thin film transistors.

4. (ORIGINAL) The display device according to claim 1, wherein the display device is an organic electroluminescent display device.

5. (ORIGINAL) The display device according to claim 1, wherein the polysilicon substrate is fabricated by an SLS (sequential lateral solidification) method.

6. (CANCELLED)

7. (PREVIOUSLY PRESENTED) The display device according to claim 1, wherein the primary crystal grain boundaries are perpendicular to the second direction of current.

8. (ORIGINAL) The display device according to claim 7, wherein a second number of the primary crystal grain boundaries exist in active channel regions of each of the second plurality of thin film transistors.

9. (CANCELLED)

10. (CANCELLED)

11. (PREVIOUSLY PRESENTED) A display device with a polysilicon substrate comprising:

a driving region;

a plurality of thin film transistors in the driving region;

primary crystal grain boundaries in the polysilicon substrate in the driving region; and

secondary crystal grain boundaries in the polysilicon substrate in the driving region;

wherein the primary crystal grain boundaries are inclined to a direction of current flowing from source to drain of each of the plurality of thin film transistors at an angle of 30° to 150° and the secondary crystal grain boundaries are substantially parallel to the current flowing from the source to the drain.

12. (PREVIOUSLY PRESENTED) A display device with a polysilicon substrate comprising:

a display region;

a driving region;

a plurality of thin film transistors formed in the display and in the driving regions;

primary and secondary crystal grain boundaries formed in the polysilicon substrate in the display region and in the driving regions;

wherein the primary crystal grain boundaries formed in the display region are inclined to a direction of current flowing from source to drain at an angle of -30° to 30° and the secondary crystal grain boundaries formed in the display region are substantially perpendicular to the current flowing from the source to the drain; and

wherein the primary crystal grain boundaries formed in the driving region are inclined to a direction of current flowing from source to drain at an angle of 30° to 150° and the secondary crystal grain boundaries formed in the driving region are substantially parallel to the current flowing from the source to the drain.